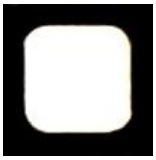
Silicon Carbide Power Schottky Diode

V_{RRM}	=	1200 V
I_F @ 25 °C	=	25 A
Q_C	=	31 nC

Features

- 1200 V Schottky rectifier
- 175 °C maximum operating temperature
- Temperature independent switching behavior
- Superior surge current capability
- Positive temperature coefficient of V_F
- Extremely fast switching speeds
- Superior figure of merit Q_C/I_F



Die Size = 2.15 mm x 2.15 mm

Advantages

- Improved circuit efficiency (Lower overall cost)
- Low switching losses
- Ease of paralleling devices without thermal runaway
- Smaller heat sink requirements
- Low reverse recovery current
- Low device capacitance
- Low reverse leakage current at operating temperature

Applications

- Power Factor Correction (PFC)
- Switched-Mode Power Supply (SMPS)
- Solar Inverters
- Wind Turbine Inverters
- Motor Drives
- Induction Heating
- Uninterruptible Power Supply (UPS)
- High Voltage Multipliers

Maximum Ratings at T_j = 175 °C, unless otherwise specified

Parameter	Symbol	Conditions	Values	Unit
Repetitive peak reverse voltage	V_{RRM}		1200	V
Continuous forward current	I_F	T_C = 25 °C, R_{thJC} = 0.8	25	A
Continuous forward current	I_F	T_C ≤ 150 °C, R_{thJC} = 0.8	10	A
RMS forward current	$I_{F(RMS)}$	T_C ≤ 150 °C, R_{thJC} = 0.8	17	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	T_C = 25 °C, t_P = 10 ms T_C = 150 °C, t_P = 10 ms	65 55	A
Non-repetitive peak forward current	$I_{F,max}$	T_C = 25 °C, t_P = 10 µs	280	A
I^2t value	$\int i^2\,dt$	T_C = 25 °C, t_P = 10 ms T_C = 150 °C, t_P = 10 ms	21 15	A^2s
Power dissipation	P_{tot}	T_C = 25 °C, R_{thJC} = 0.8	190	W
Operating and storage temperature	T_j , T_{stg}		-55 to 175	°C

Electrical Characteristics at T_j = 175 °C, unless otherwise specified

Parameter	Symbol	Conditions		Values min.	Values typ.	Values max.	Unit
Diode forward voltage	V_F	I_F = 10 A, T_j = 25 °C I_F = 10 A, T_j = 175 °C			1.5 2.6	1.8 3.0	V
Reverse current	I_R	V_R = 1200 V, T_j = 25 °C V_R = 1200 V, T_j = 175 °C			5 10	50 100	µA
Total capacitive charge	Q_C	$I_F \le I_{F,MAX}$ dI_F/dt = 200 A/µs T_j = 175 °C	V_R = 400 V V_R = 960 V		31 52		nC
Switching time	t_s		V_R = 400 V V_R = 960 V		< 25		ns
Total capacitance	C	V_R = 1 V, f = 1 MHz, T_j = 25 °C V_R = 400 V, f = 1 MHz, T_j = 25 °C V_R = 1000 V, f = 1 MHz, T_j = 25 °C			490 45 33		pF

Figures:

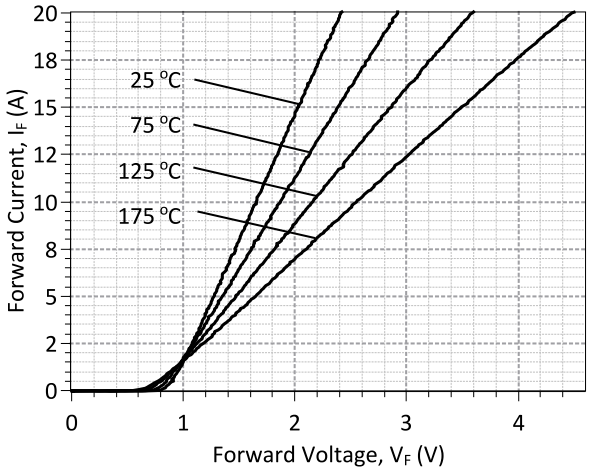


Figure 1: Typical Forward Characteristics

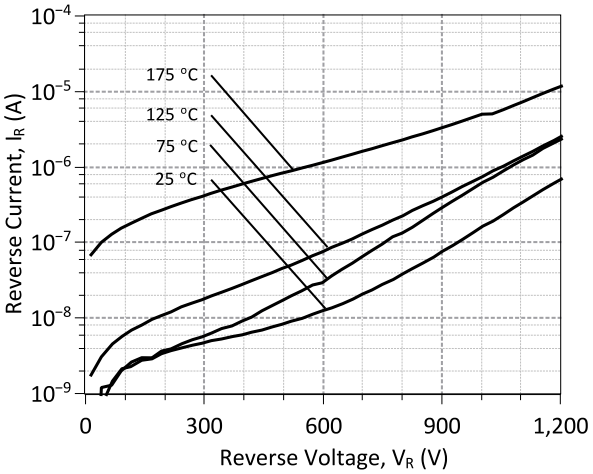


Figure 2: Typical Reverse Characteristics

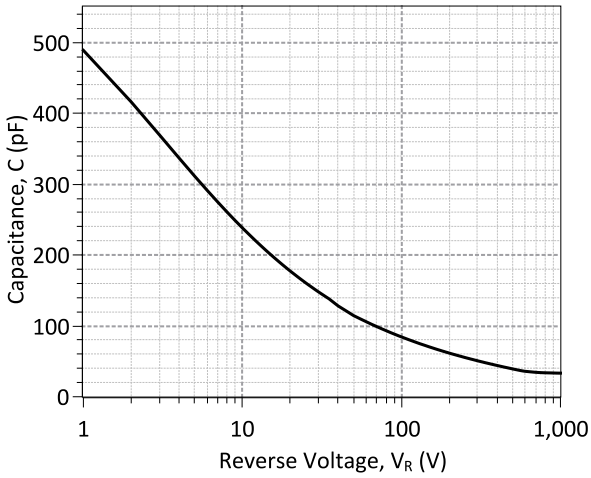


Figure 3: Typical Junction Capacitance vs Reverse Voltage Characteristics

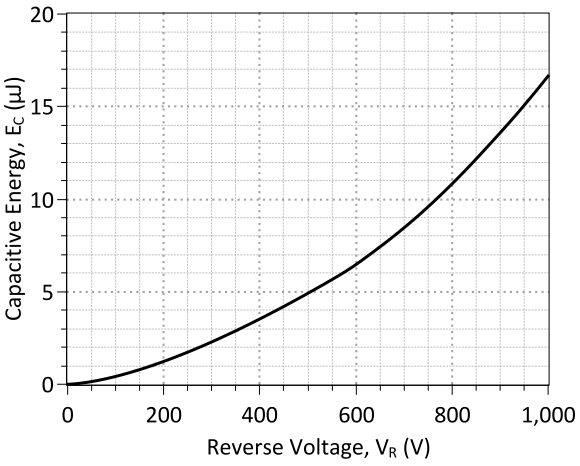
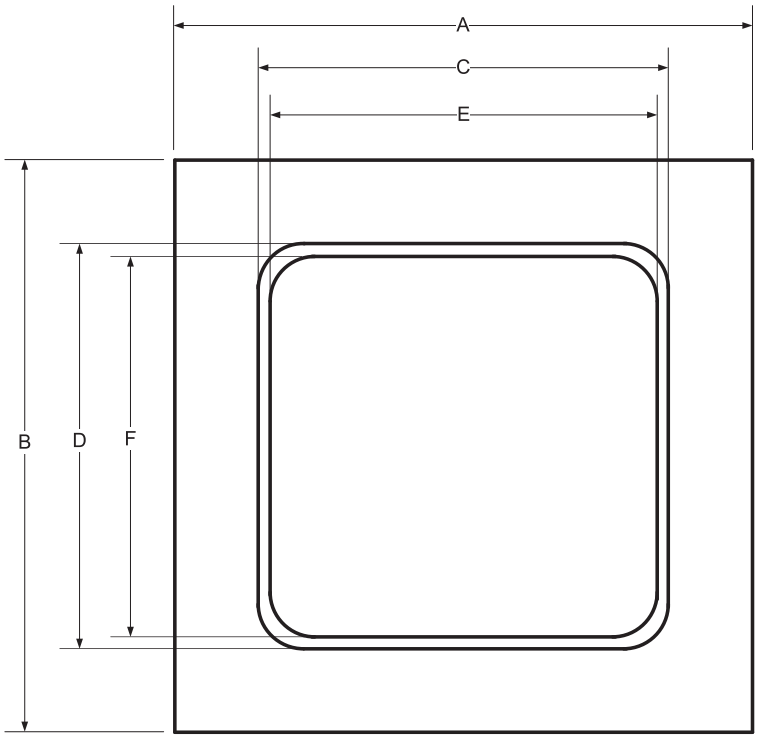


Figure 4: Typical Capacitive Energy vs Reverse Voltage Characteristics

Mechanical Parameters

Die Dimensions	2.15 x 2.15	mm^2
Anode pad size	1.93 x 1.93	
Die Thickness	360	µm
Wafer Size	100	mm
Flat Position	0	deg
Die Frontside Passivation	Polyimide	
Anode Pad Metallization	4000 nm Al	
Backside Cathode Metallization	400 nm Ni + 200 nm Au	
Die Attach	Electrically conductive glue or solder	
Wire Bond	Al ≤ 350 µm	
Reject ink dot size	Φ ≥ 0.3 mm	
Recommended storage environment	Store in original container, in dry nitrogen, < 6 months at an ambient temperature of 23 °C	

Chip Dimensions:



DIE	A [mm]	2.15
	B [mm]	2.15
METAL	C [mm]	1.93
	D [mm]	1.93
WIRE BONDABLE	E [mm]	1.85
	F [mm]	1.85

Revision History			
Date	Revision	Comments	Supersedes
2015/02/12	3	Inserted Mechanical Parameters	
2014/09/12	2	Updated Electrical Characteristics	
2013/11/12	1	Updated Electrical Characteristics	
2013/10/15	0	Initial release	

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SPICE Model Parameters

This is a secure document. Please copy this code from the SPICE model PDF file on our website (http://www.genesicsemi.com/images/hit_sic/baredie/schottky/GB10SLT12-CAL_SPICE.pdf) into LTSPICE (version 4) software for simulation of the GB10SLT12-CAL.

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*     MODEL OF GeneSiC Semiconductor Inc.
*
*     $Revision:   1.0           $
*     $Date:   20-SEP-2013       $
*
*     GeneSiC Semiconductor Inc.
*     43670 Trade Center Place Ste. 155
*     Dulles, VA 20166
*
*     COPYRIGHT (C) 2013 GeneSiC Semiconductor Inc.
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*
* These models are provided "AS IS, WHERE IS, AND WITH NO WARRANTY
* OF ANY KIND EITHER EXPRESSED OR IMPLIED, INCLUDING BUT NOT LIMITED
* TO ANY IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A
* PARTICULAR PURPOSE."
* Models accurate up to 2 times rated drain current.
*
* Start of GB10SLT12-CAL SPICE Model
*
.SUBCKT GB10SLT12 ANODE KATHODE
D1 ANODE KATHODE GB10SLT12_SCHOTTKY
D2 ANODE KATHODE GB10SLT12_PIN
.MODEL GB10SLT12_SCHOTTKY D
+ IS       4.55E-15        RS         0.0736
+ N        1               IKF        1000
+ EG       1.2             XTI        -2
+ TRS1     0.0054347826    TRS2       2.71739E-05
+ CJO      6.40E-10        VJ         0.469
+ M        1.508           FC         0.5
+ TT       1.00E-10        BV         1200
+ IBV      1.00E-03        VPK        1200
+ IAVE     10              TYPE       SiC_Schottky
+ MFG      GeneSiC_Semi
.MODEL GB10SLT12_PIN D
+ IS       1.54E-22        RS         0.19
+ TRS1     -0.004          N          3.941
+ EG       3.23            IKF        19
+ XTI      0               FC         0.5
+ TT       0               BV         1200
+ IBV      1.00E-03        VPK        1200
+ IAVE     10              TYPE       SiC_PiN
.ENDS
*
* End of GB10SLT12-CAL SPICE Model
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